

74V2T384

DUAL HIGH SPEED BUS SWITCH

- HIGH SPEED: t_{PD} = 0.5ns (TYP.) at V_{CC} = 5V
- COMPATIBLE WITH TTL LEVEL
- LOW POWER DISSIPATION:
 I_{CC} = 1μA(MAX.) at T_A = 25°C
- LOW "ON" RESISTANCE at V_{CC} =5.0V: $R_{ON} = 7\Omega$ (TYP.) $V_{IN} = 0V I_{I/O} = 30mA$ $R_{ON} = 20\Omega$ (TYP.) $V_{IN} = 2.4V I_{I/O} = 10mA$
- OPERATING VOLTAGE RANGE:
 V_{CC} (OPR) = 4.0V TO 5.5V
- 5V TOLERANT ON CONTROL PIN
- IMPROVED LATCH-UP IMMUNITY

DESCRIPTION

The 74V2T384 is an advanced high-speed CMOS DUAL HIGH SPEED BUS SWITCH fabricated in silicon gate C²MOS technology. It's designed to operate from 4.5V to 5.5V, making this device ideal for portable applications. It's offers 7 Ω Resistance typical value at V_{CC}=4.5V. Additional key feature are fast switching speed (t_{3N1}=2.8ns,



ORDER CODES

PACKAGE	T&R
SOT?3.PL	74\2T364STR

toFF=3.3r Typical) and Low Power Consumption.

The \overrightarrow{OE} input is provided to control the switch; the switch is \overrightarrow{ON} when the \overrightarrow{OE} input is held low and \overrightarrow{OFF} when \overrightarrow{CE} is held high.

It's available in the commercial and extended temperature range in SOT23-8L package.

PLU CONNECTION FND LEC LOGIC SYMBOLS

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INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 5	1I/O, 2I/O	Independent Input/Output
2, 6	10/I, 20/I	Independent Output/Input
7, 3	10E, 20E	Enable Input (Active HIGH)
4	GND	Ground (0V)
8	V _{CC}	Positive Supply Voltage

TRUTH TABLE

OE	SWITCH FUNCTION
L	1/
Н	051 *
* High Impedance State	90
01	16

57

ABSOLUTE MAXIMUM RATINGS

Parameter	Value	Unit
Supply Voltage	-0.5 to +7.0	V
DC Input Voltage	-0.5 to V _{CC} + 0.5	V
DC Control Input Voltage	-0.5 to +7.0	V
DC Output Voltage	-0.5 to V _{CC} + 0.5	V
DC Input Diode Current	± 20	mA
DC Control Input Diode Current	- 20	mA
DC Output Diode Current	± 20	mA
DC Output Current	± 50	mA
DC V _{CC} or Ground Cuiront	± 50	mA
Storage Temperature	-65 to +150	°C
Lead Temperature (10 sec)	300	°C
	Supply Voltage DC Input Voltage DC Control Input Voltage DC Output Voltage DC Input Diode Current DC Control Input Diode Current DC Output Diode Current DC Output Diode Current DC Output Current DC Output Current Storage Temperature	Supply Voltage $-0.5 \text{ to } +7.0$ DC Input Voltage $-0.5 \text{ to } V_{CC} + 0.5$ DC Control Input Voltage $-0.5 \text{ to } V_{CC} + 0.5$ DC Output Voltage $-0.5 \text{ to } V_{CC} + 0.5$ DC Input Diode Current ± 20 DC Control Input Diode Current -20 DC Output Diode Current ± 20 DC Output Diode Current ± 50 DC Output Current ± 50 Storage Temperature $-65 \text{ to } +150$

Absolute Maximum re- tings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

RECON'MENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	4.0 to 5.5	V
VI	Input Voltage	0 to V _{CC}	V
V _{IC}	Control Input Voltage	0 to 5.5	V
Vo	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
dt/dv	Input Rise and Fall Time (note 1) $V_{CC} = 5.0V$	0 to 20	ns/V

1) V_{IN} from 0.8V to 2V on control pin

DC SPECIFICATIONS

		٦	est Condition				Value				
Symbol	Parameter	v _{cc}		Т	_A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V _{IH}	High Level Input Voltage	5.0 ^(*)		2			2		2		V
V _{IL}	Low Level Input Voltage	5.0 ^(*)				0.8		0.8		0.8	V
V _{IH}	High Level Input Voltage	4.0		2			2		2		V
V _{IL}	Low Level Input Voltage	4.0				0.8		0.8		0.8	V
R _{ON}	ON Resistance	4.5	$V_{IC} = V_{IL}$ $V_{I/O} = GND$ $I_{I/O} \le 30mA$		7			10	JC	15	V
R _{ON}	ON Resistance	4.5	$V_{IC} = V_{IL}$ $V_{I/O} = 2.4V$ $I_{I/O} \le 10mA$		20		91	4)		60	V
I _{OFF}	Input/Output Leakage Current (SWITCH OFF)	5.5	$V_{OS} = V_{CC} \text{ to GND}$ $V_{IS} = V_{CC} \text{ to GND}$ $V_{IC} = V_{IH}$	C	019	-0.1		± 1	200	± 10	μA
I _{IN}	Control Input Leakage Current	0 to 5.5	V _{IC} = 5.5V or G₩D	0		± 0.1	Y	± 1.0		± 1.0	μA
I _{CC}	Quiescent Supply Current	5.5	$V_{I} = V_{CC}$ or GND			1		10		20	μA
ΔI_{CC}	Increase Quiescent Supply Current per Control Input	5.5	V _{IC} = V _C -2.1V wher V _{IC} = V _{CC} or GND	10 ²	, O	1.35		2.5		3.5	mA

AC ELECTRICAL CHAIRACTERISTICS ($C_L = 50pF$, Input $t_r = t_f = 3ns$)

	N N	т	est Condition				Value				
Symbol	bol Farameter		V _{cc}		T _A = 25°C			-40 to 85°C		-55 to 125°C	
\sim	~ 10	(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t-p	Delay Time	5.0 ^(*)	$t_r = t_r = 6ns$		0.5	0.8		1.0		1.5	ns
t _{PLZ} t _{PHZ}	Output Disable Time	5.0 ^(*)	$R_L = 500 \Omega$ $V_{IN} = 2.4 V$		3.8	6.5		9.0		10.0	ns
t _{PZL} t _{PZH}	Output Enable Time	5.0 ^(*)	$R_L = 1 K\Omega$ $V_{IN} = 2.4 V$		3.3	5.0		7.5		8.5	ns

(*) Voltage range is $5.0V \pm 0.5V$

57

CAPACITIVE CHARACTERISTICS

		Test Condition				Value					
Symbol	I Parameter		Т	A = 25°	°C	-40 to	o 85°C	-55 to	125°C	Unit	
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
C _{IN}	Input Capacitance			4	10		10		10	р	
C _{I/O}	Output Capacitance			7						р	
C _{PD}	Power Dissipation Capacitance (note 1)			3						р	
							2	JUC			
						2	0	<i>.</i>)	
					10						
			C	0			<i>'</i> 0')			
			0,0,0	301		<i>P</i>	10,				
			0,0,0	301	ete	, <i>P</i>	^c Or				
		ct(S)-	0,0,0	;0 ¹ ;0 ¹	ete	,P	lor				
		duct(S)		;01 ;01	ete	,P'	100)			
	Pio	duct(S)	0,0,0	;0 ¹ ;0 ¹	ete	Ŗ	COL				
	etepro	duct(S)	0,0,	501	ete	Ŗ					
60	etepro	duct(s)	0,05	30	ete	Ŗ					
050	lete Pro	duct(S)	0,05	50	ete	Ŗ					
050	ete Pro	ducils	0,0,	501	ete	Ŗ					
050	lete Pro	duct(s)	0,05	501	ete	Ŗ					
050	lete Pro	duct(s)	0,05	501	ete	Ŗ					

DIM.		mm.		mils				
Diwi.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.		
А	0.90		1.45	35.4		57.1		
A1	0.00		0.15	0.0		5.9		
A2	0.90		1.30	35.4		51.2		
b	0.22		0.38	8.6		14.9		
С	0.09		0.20	3.5	40	7.8		
D	2.80		3.00	110.2	100	118.1		
Е	2.60		3.00	102.3		118.1		
E1	1.50		1.75	59.0		68.8		
е	0	.65	->>5	0	25.6			
e1		1.95	Ob		76.7			
L	0.35		0.55	13.7		21.6		







	Tape & Reel SOT23-xL MECHANICAL DATA								
DIM		mm.		inch					
DIM.	MIN.	ТҮР	MAX.	MIN.	TYP.	MAX.			
А			180			7.086			
С	12.8	13.0	13.2	0.504	0.512	0.519			
D	20.2			0.795					
Ν	60			2.362					
Т			14.4			0.5ò7			
Ao	3.13	3.23	3.33	0.123	0.127	0.131			
Во	3.07	3.17	3.27	0.120	0.124	0.128			
Ko	1.27	1.37	1.47	0.050	0.054	0.0.58			
Po	3.9	4.0	4.1	0.155	0.157	0.161			
Р	3.9	4.0	4.1	0.153	0.157	0.161			



74V2T384

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57